

BS250FTA Datasheet

P-Channel 60 V (D-S) MOSFET

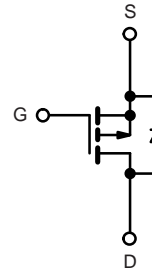
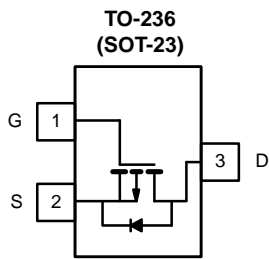
| PRODUCT SUMMARY | | | |
|-----------------|---------------------------|------------------|------------|
| V_{DS} (V) | $R_{DS(on)}$ (Ω) | $V_{GS(th)}$ (V) | I_D (mA) |
| - 60 | 3 at $V_{GS} = - 10$ V | - 1 to - 3 | -500 |

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- High-Side Switching
- Low On-Resistance: 3 Ω
- Low Threshold: - 2 V (typ.)
- Fast Switching Speed: 20 ns (typ.)
- Low Input Capacitance: 20 pF (typ.)
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT



P-Channel MOSFET

| ABSOLUTE MAXIMUM RATINGS $T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted | | | |
|--|----------------|-----------------------------------|--------------------|
| Parameter | Symbol | Limit | Unit |
| Drain-Source Voltage | V_{DS} | - 60 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | |
| Continuous Drain Current ^a | I_D | $T_A = 25\text{ }^\circ\text{C}$ | - 500 |
| | | $T_A = 100\text{ }^\circ\text{C}$ | - 350 |
| Pulsed Drain Current ^b | I_{DM} | -1500 | mA |
| Power Dissipation ^a | P_D | $T_A = 25\text{ }^\circ\text{C}$ | 460 |
| | | $T_A = 100\text{ }^\circ\text{C}$ | 240 |
| Maximum Junction-to-Ambient ^a | R_{thJA} | 350 | $^\circ\text{C/W}$ |
| Operating Junction and Storage Temperature Range | T_J, T_{stg} | - 55 to 150 | $^\circ\text{C}$ |

Notes:

a. Surface mounted on FR4 board.

b. Pulse width limited by maximum junction temperature.

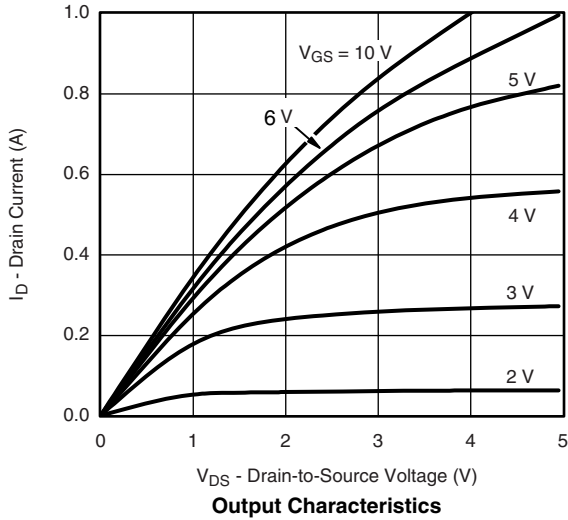
| SPECIFICATIONS $T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted | | | | | | |
|---|--------------|--|--------|-------------------|-----------|---------------|
| Parameter | Symbol | Test Conditions | Limits | | | Unit |
| | | | Min. | Typ. ^a | Max. | |
| Static | | | | | | |
| Drain-Source Breakdown Voltage | V_{DS} | $V_{GS} = 0\text{ V}, I_D = -10\text{ }\mu\text{A}$ | - 60 | | | V |
| Gate-Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$ | - 1 | | - 3 | |
| Gate-Body Leakage | I_{GSS} | $V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$ | | | ± 10 | μA |
| | | $V_{DS} = 0\text{ V}, V_{GS} = \pm 10\text{ V}$ | | | ± 200 | |
| | | $V_{DS} = 0\text{ V}, V_{GS} = \pm 10\text{ V}, T_J = 85\text{ }^\circ\text{C}$ | | | ± 500 | nA |
| | | $V_{DS} = 0\text{ V}, V_{GS} = \pm 5\text{ V}$ | | | ± 100 | |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = -60\text{ V}, V_{GS} = 0\text{ V}$ | | | - 25 | |
| | | $V_{DS} = -60\text{ V}, V_{GS} = 0\text{ V}, T_J = 85\text{ }^\circ\text{C}$ | | | - 250 | |
| On-State Drain Current ^a | $I_{D(on)}$ | $V_{GS} = -10\text{ V}, V_{DS} = -4.5\text{ V}$ | - 50 | | | mA |
| | | $V_{GS} = -10\text{ V}, V_{DS} = -10\text{ V}$ | - 600 | | | |
| Drain-Source On-Resistance ^a | $R_{DS(on)}$ | $V_{GS} = -4.5\text{ V}, I_D = -25\text{ mA}$ | | 4 | | Ω |
| | | $V_{GS} = -10\text{ V}, I_D = -100\text{ mA}$ | | 3 | | |
| | | $V_{GS} = -10\text{ V}, I_D = -100\text{ mA}, T_J = 125\text{ }^\circ\text{C}$ | | 9 | | |
| Forward Transconductance ^a | g_{fs} | $V_{DS} = -10\text{ V}, I_D = -100\text{ mA}$ | 80 | | | mS |
| Diode Forward Voltage | V_{SD} | $I_S = -100\text{ mA}, V_{GS} = 0\text{ V}$ | | | - 1.4 | V |
| Dynamic | | | | | | |
| Total Gate Charge | Q_g | $V_{DS} = -30\text{ V}, V_{GS} = -15\text{ V}$ $I_D \cong -100\text{ mA}$ | | 2.0 | | nC |
| Gate-Source Charge | Q_{gs} | | | 1.2 | | |
| Gate-Drain Charge | Q_{gd} | | | 0.8 | | |
| Input Capacitance | C_{iss} | $V_{DS} = -25\text{ V}, V_{GS} = 0\text{ V}$ $f = 1\text{ MHz}$ | | 23 | | pF |
| Output Capacitance | C_{oss} | | | 10 | | |
| Reverse Transfer Capacitance | C_{rss} | | | 5 | | |
| Switching^b | | | | | | |
| Turn-On Time | $t_{d(on)}$ | $V_{DD} = -25\text{ V}, R_L = 150\text{ }\Omega$ $I_D \cong -200\text{ mA}, V_{GEN} = -10\text{ V}, R_g = 10\text{ }\Omega$ | | 20 | | ns |
| Turn-Off Time | $t_{d(off)}$ | | | 35 | | |

Notes:

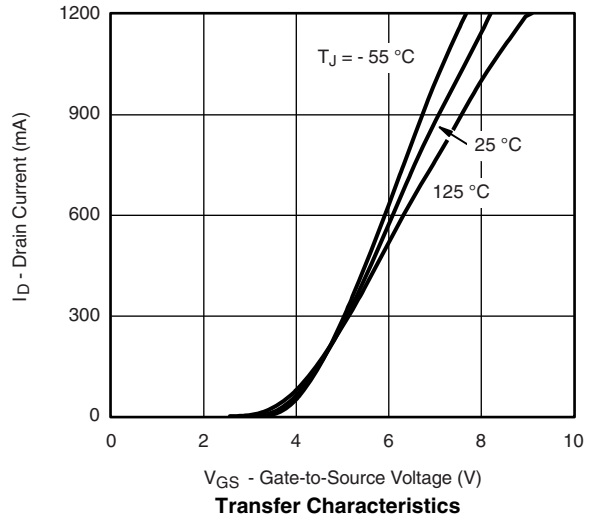
- a. Pulse test: $PW \leq 300\text{ }\mu\text{s}$ duty cycle $\leq 2\%$.
 b. Switching time is essentially independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

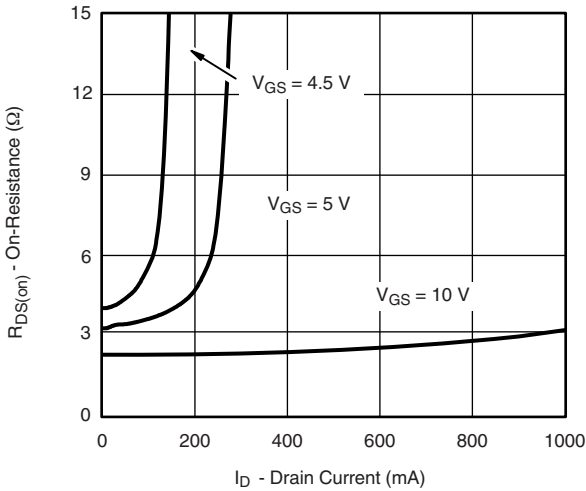
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



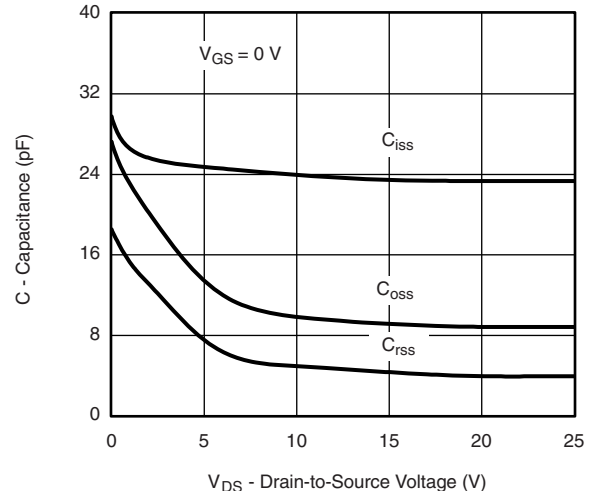
Output Characteristics



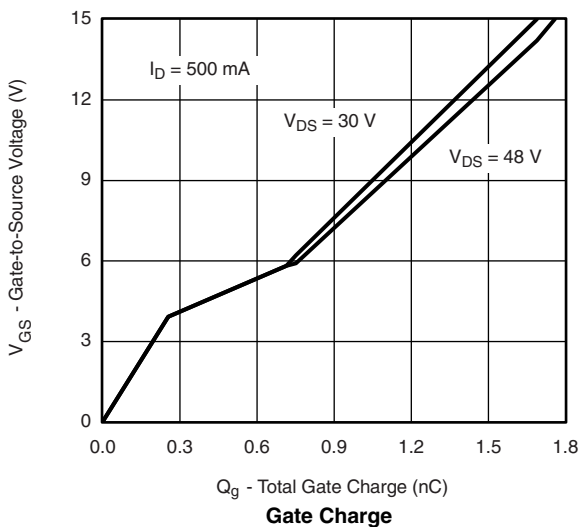
Transfer Characteristics



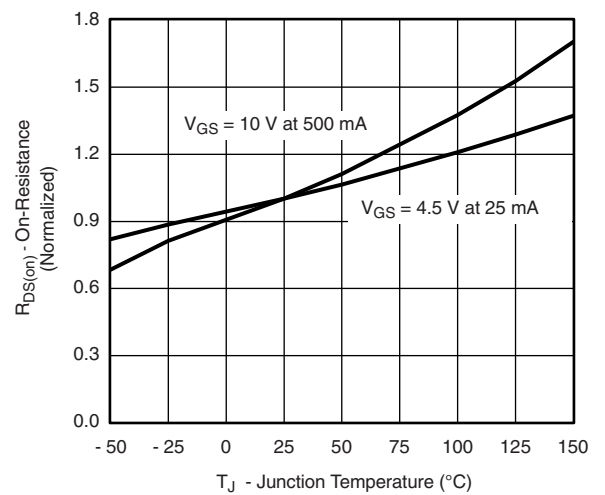
On-Resistance vs. Drain Current



Capacitance

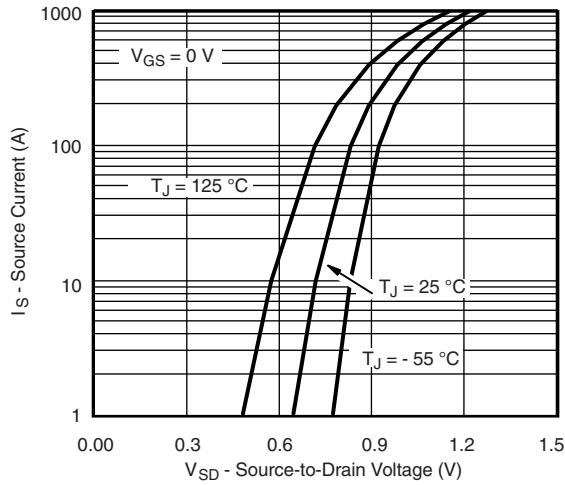


Gate Charge

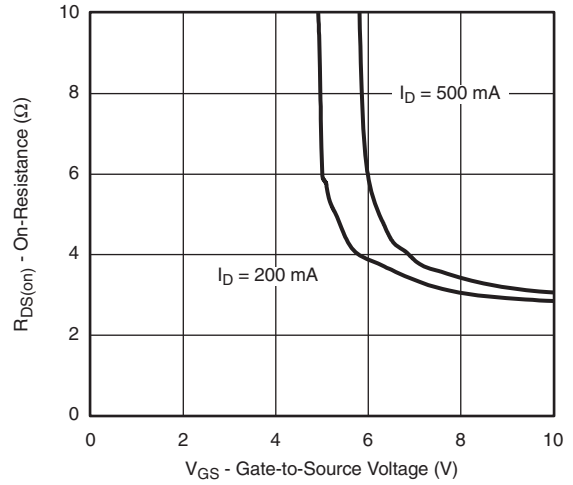


On-Resistance vs. Junction Temperature

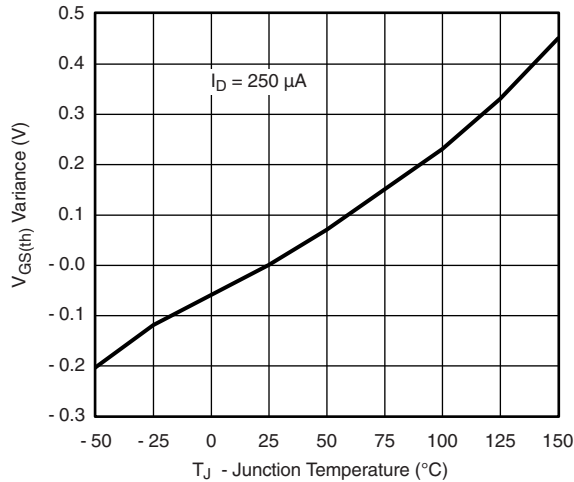
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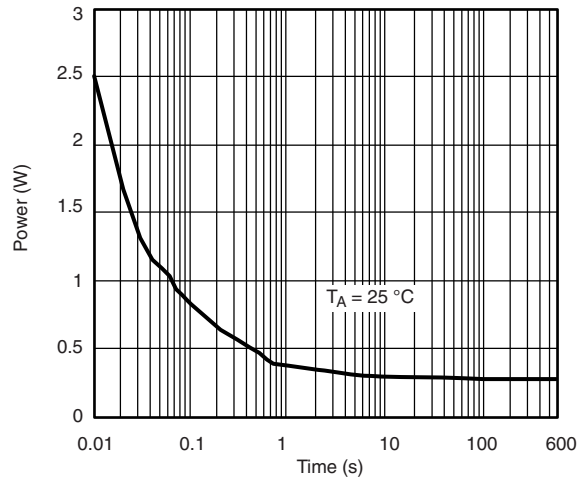
Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-Source Voltage



Threshold Voltage Variance Over Temperature

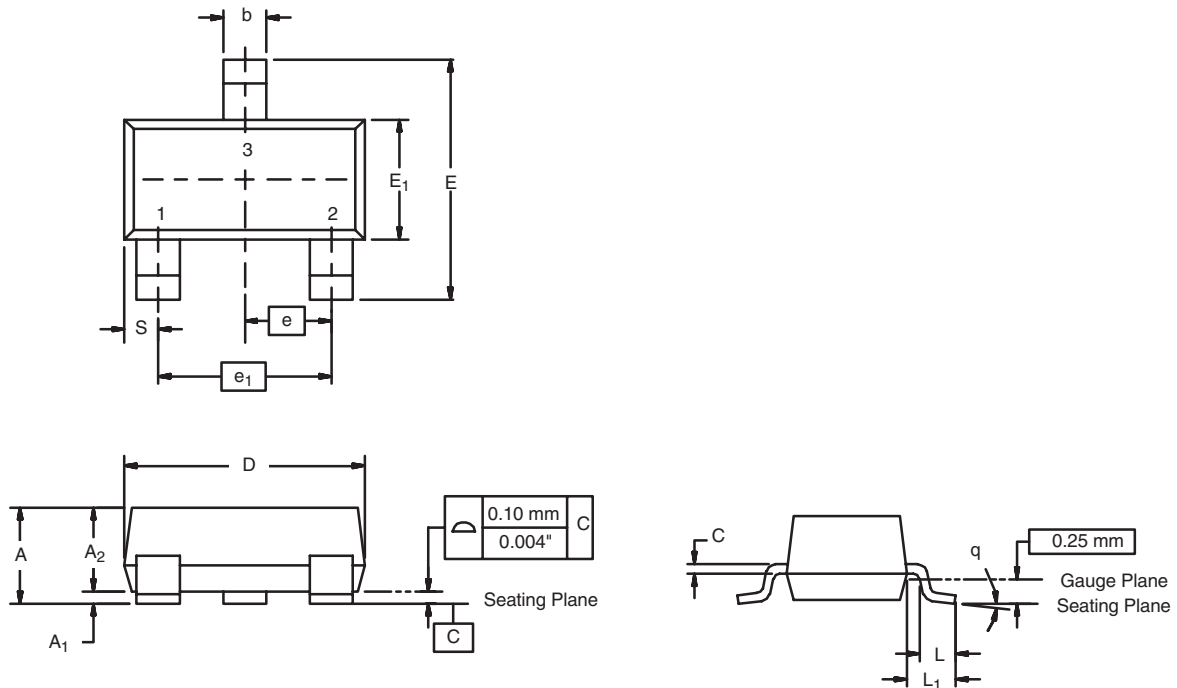


Single Pulse Power, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Ambient

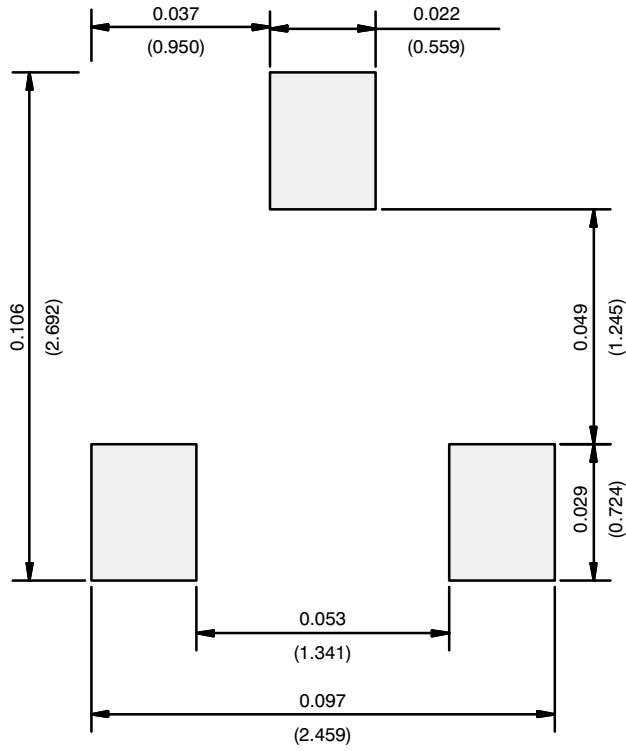
SOT-23 (TO-236): 3-LEAD



| Dim | MILLIMETERS | | INCHES | |
|----------------|-------------|------|------------|-------|
| | Min | Max | Min | Max |
| A | 0.89 | 1.12 | 0.035 | 0.044 |
| A ₁ | 0.01 | 0.10 | 0.0004 | 0.004 |
| A ₂ | 0.88 | 1.02 | 0.0346 | 0.040 |
| b | 0.35 | 0.50 | 0.014 | 0.020 |
| c | 0.085 | 0.18 | 0.003 | 0.007 |
| D | 2.80 | 3.04 | 0.110 | 0.120 |
| E | 2.10 | 2.64 | 0.083 | 0.104 |
| E ₁ | 1.20 | 1.40 | 0.047 | 0.055 |
| e | 0.95 BSC | | 0.0374 Ref | |
| e ₁ | 1.90 BSC | | 0.0748 Ref | |
| L | 0.40 | 0.60 | 0.016 | 0.024 |
| L ₁ | 0.64 Ref | | 0.025 Ref | |
| S | 0.50 Ref | | 0.020 Ref | |
| q | 3° | 8° | 3° | 8° |

ECN: S-03946-Rev. K, 09-Jul-01
DWG: 5479

RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads
Dimensions in Inches/(mm)

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